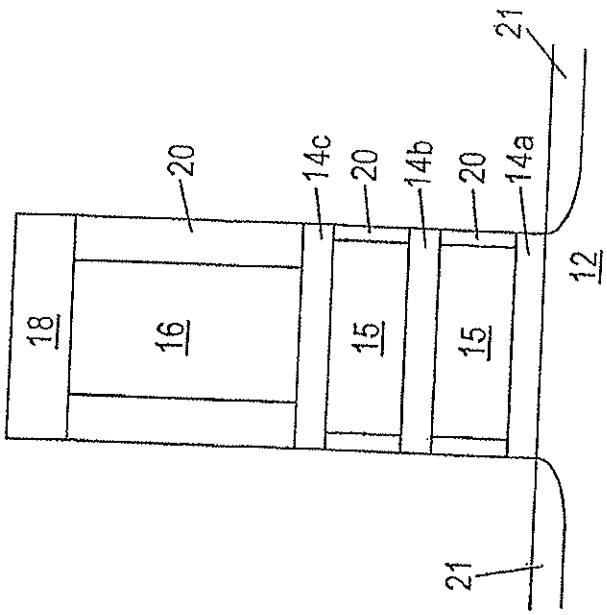

21
20
14c
20
14b
20
14a
18
16
15
15
12
21

Fig. 2

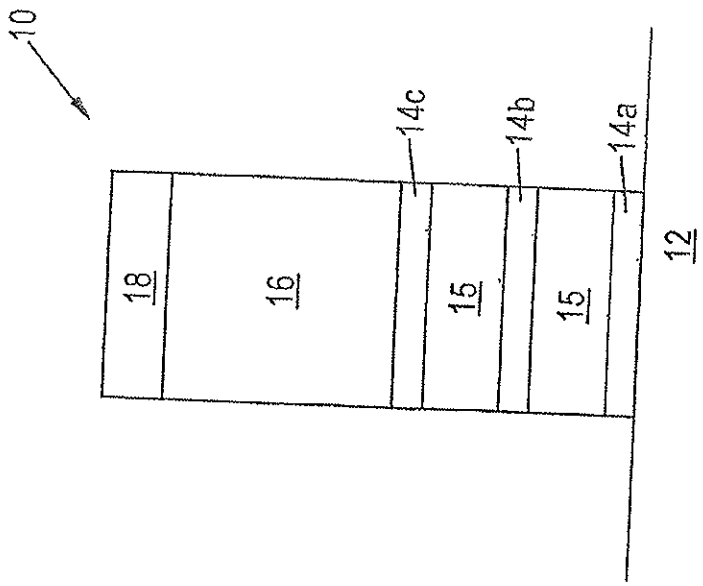

10
14c
14b
14a
18
16
15
15
12

Fig. 1

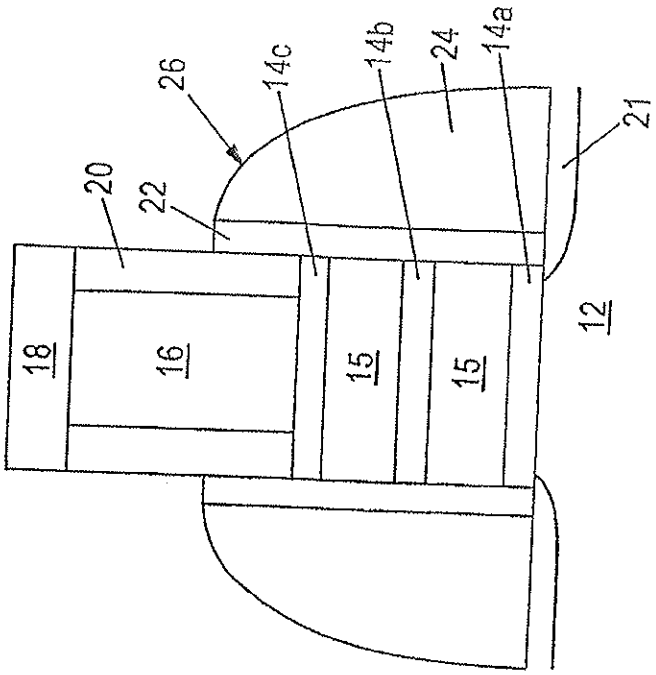

26
14c
14b
24
14a
21
20
22
18
16
15
15
12

Fig. 4

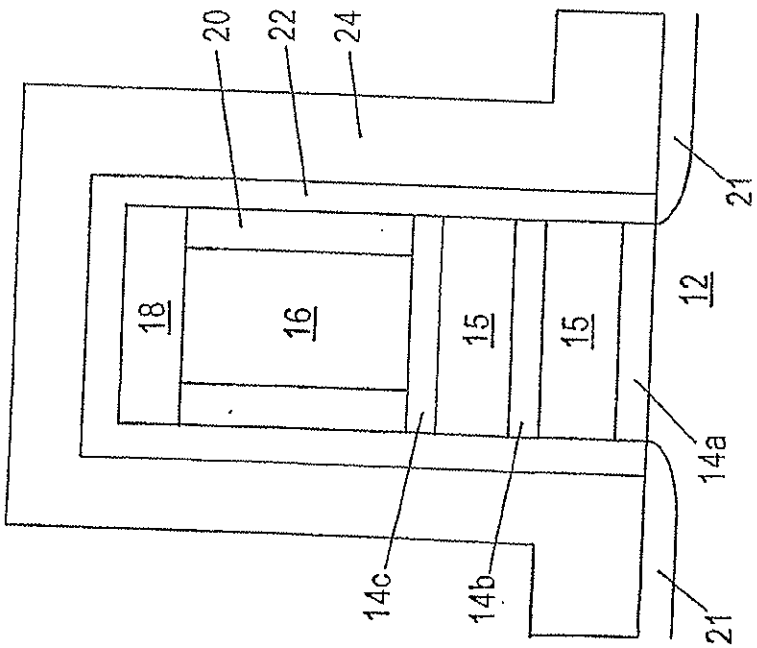

20
22
24
21
18
16
15
15
12
14a
14c
14b
21

Fig. 3

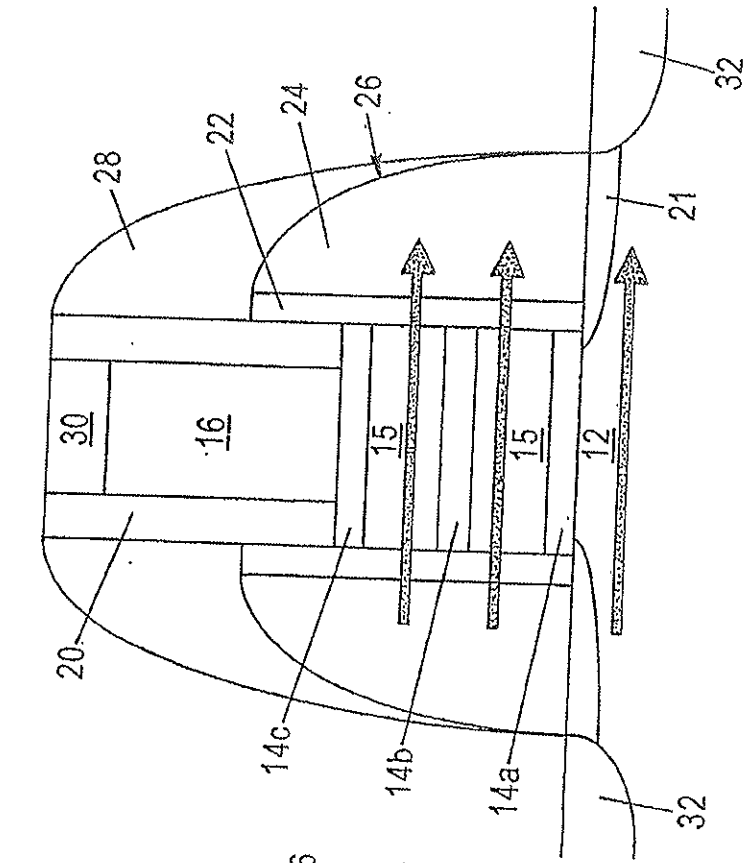

28
22
24
26
32
21
30
16
15
15
12
20
14c
14b
14a
32

Fig. 6

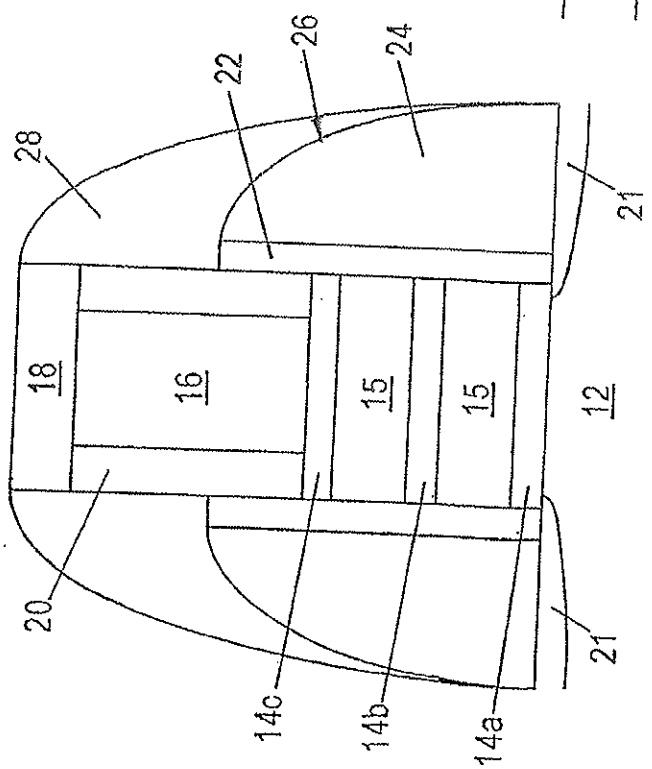

28
22
26
24
21
18
16
15
15
12
20
14c
14b
14a
21

Fig. 5

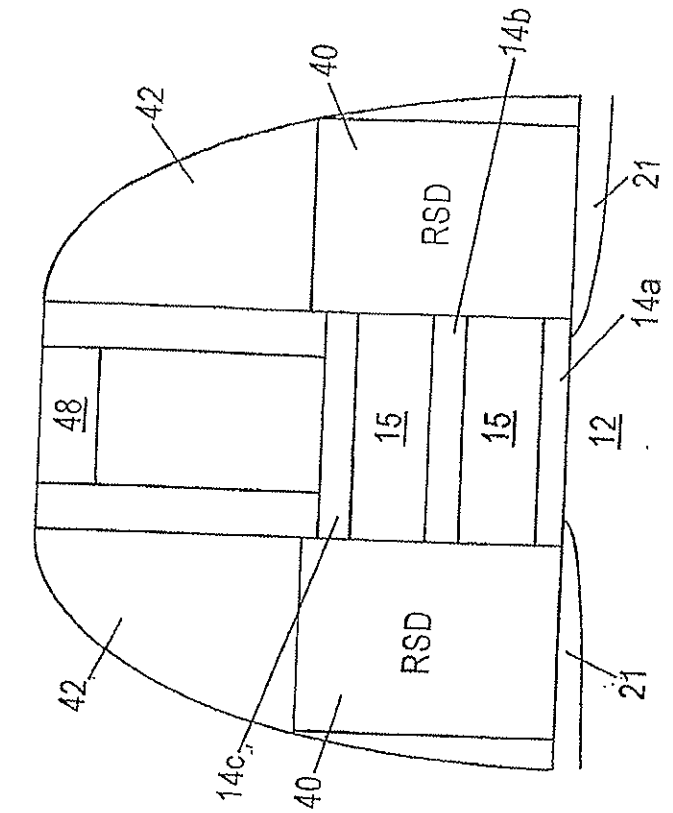

42
40
14b
21
RSD
14a
48
15
15
12
42
RSD
21
14c
40

Fig. 8

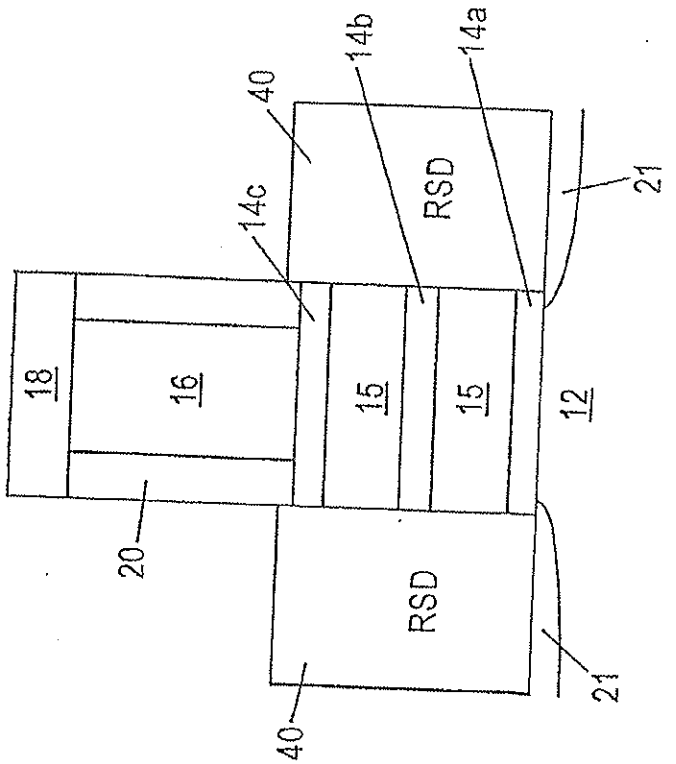

14b
14a
40
21
RSD
14c
18
16
15
15
12
20
RSD
40
21

Fig. 7

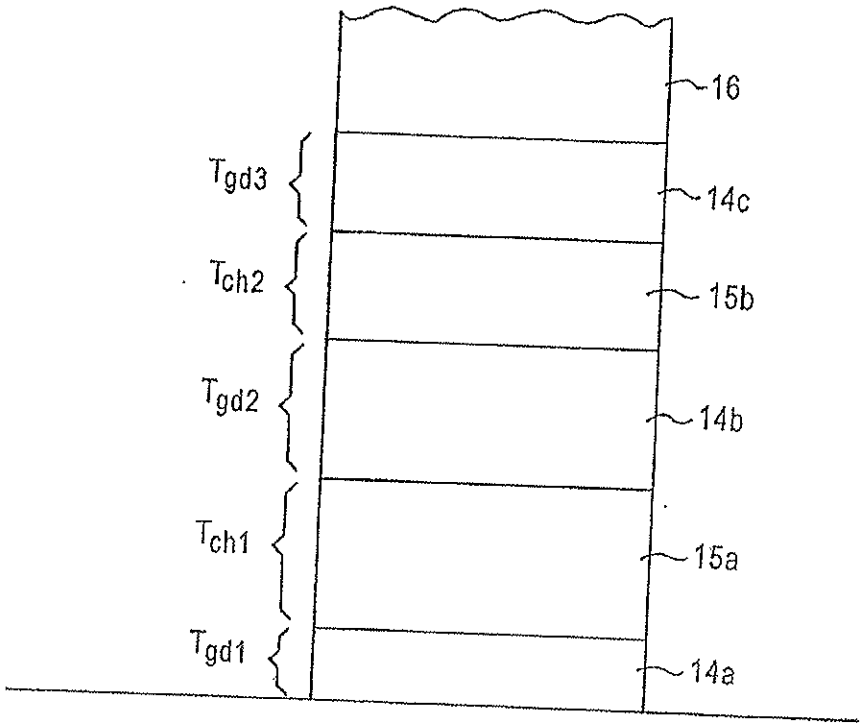


Fig. 9

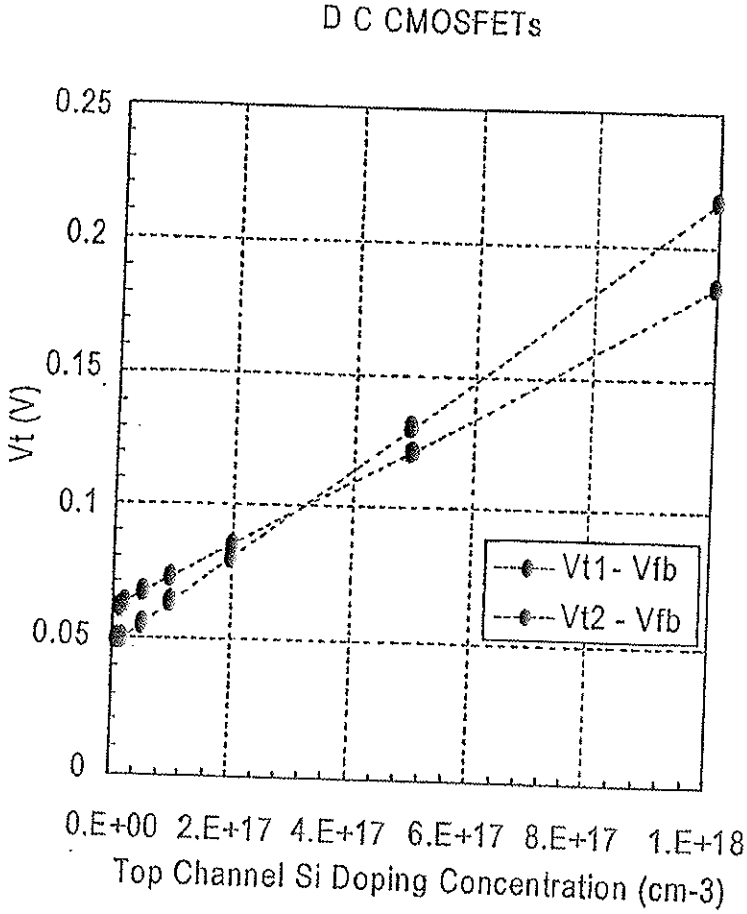

D C CMOSFETs
0.25
0.2
0.15
0.1
0.05
0
Vt (V)
Vt1 - Vfb
Vt2 - Vfb
0.E+00 2.E+17 4.E+17 6.E+17 8.E+17 1.E+18
Top Channel Si Doping Concentration (cm-3)

Fig. 10

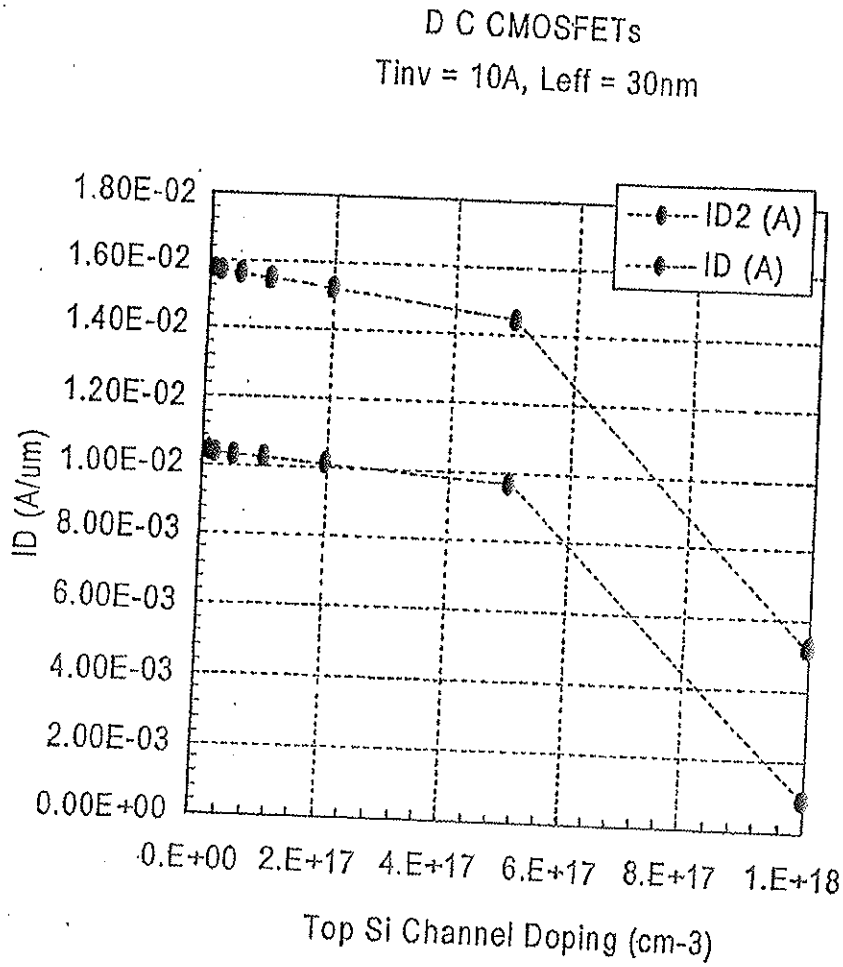

D C CMOSFETs
Tinv = 10A, Leff = 30nm
ID2 (A)
ID (A)
ID (A/um)
1.80E-02
1.60E-02
1.40E-02
1.20E-02
1.00E-02
8.00E-03
6.00E-03
4.00E-03
2.00E-03
0.00E+00
0.E+00
2.E+17
4.E+17
6.E+17
8.E+17
1.E+18
Top Si Channel Doping (cm-3)

Fig. 11